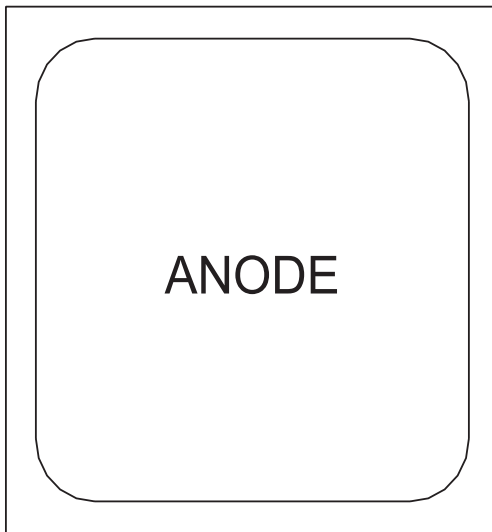


**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	87 x 87 MILS
Die Thickness	10.4 MILS
Anode Bonding Pad Area	69.5 x 69.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centrasemi.com](http://www.centrasemi.com)

**GROSS DIE PER 4 INCH WAFER**

1,490

**PRINCIPAL DEVICE TYPES**

1N5400 thru 1N5408  
1N5550 thru 1N5554  
1N5624 thru 1N5627  
CMR3-02 Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

[www.centrasemi.com/chip](http://www.centrasemi.com/chip)

R1 (1-August 2002)